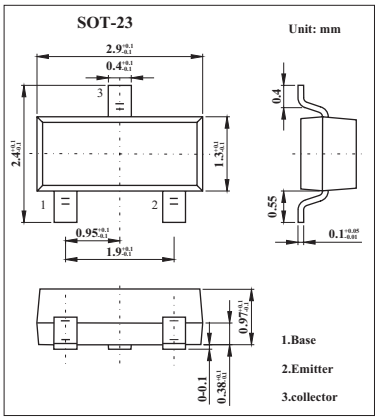
Silicon PNP Epitaxial Planar Type

2SC2405



■ Features

- Low noise voltage NV.
- High forward current transfer ratio hFE.
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	35	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA
Peak collector current	I_{CP}	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage	V_{CBO}	I_C = 10 μA, I_E = 0	35			V
Collector-emitter voltage	V_{CEO}	I_C = 2 mA, I_B = 0	35			V
Emitter-base voltage	V_{EBO}	I_E = 10 μA, I_C = 0	5			V
Base-emitter voltage	V_{BE}	V_{CE} = 1 V, I_C = 100 mA		0.7	1.0	V
Collector-base cutoff current	I_{CBO}	V_{CB} = 10 V, I_E = 0			0.1	μA
Collector-emitter cutoff current	I_{CEO}	V_{CE} = 10 V, I_B = 0			1	μA
Forward current transfer ratio	h_{FE}	V_{CE} = 5 V, I_C = 2 mA	180		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 100 mA, I_B = -10 mA			0.6	V
Transition frequency	f_T	V_{CB} = 5 V, I_E = -2 mA, f = 200 MHz		200		MHz
Noise voltage	NV	V_{CE} = 10 V, I_C = 1 mA, G_V = 80 dB R_g = 100 kΩ, Function = FLAT		110		mV

■ hFE Classification

Marking	SR	SS	ST
hFE	180～360	260～520	360～700